NSN 5961-01-058-6624

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View Online at https://aerobasegroup.com/nsn/5961-01-058-6624 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.300 inches Overall Diameter: 0.830 inches **Mounting Facility Quantity:** 2 **Internal Configuration:** Junction contact-darlington connected Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Mounting hardware **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 collector to base voltage, dc and 60.0 collector to emitter voltage/static/base open and 5.0 emitter to base voltage, dc **Current Rating Per Characteristic:** Between 1.00 amperes source cutoff current and 30.00 amperes source cutoff current **Power Rating Per Characteristic:** 150.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Test Data Document:** 30003-446as207 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure:**

No Fiig:

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Demilitarization: